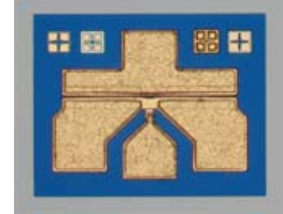


Low Noise and Medium Power GaAs FETs

FEATURES

- Via holes for source grounding
- Low Noise Figure: $NF = 0.5$ dB Typical at 12 GHz
- High Associated Gain: $G_a = 13$ dB Typical at 12 GHz
- High Dynamic Range: 1 dB Compression Power $P_{-1} = 18.5$ dBm at 12 GHz
- Breakdown Voltage: $BV_{DGO} \geq 9$ V
- $L_g = 0.25 \mu\text{m}$, $W_g = 160 \mu\text{m}$
- All-Gold Metallization for High Reliability
- Tight V_p ranges control
- High RF input power handling capability
- 100 % DC Tested

PHOTO ENLARGEMENT



DESCRIPTION

The TC1101V is the same as TC1101 except via holes in the source pads for reducing the grounding inductance. It can be used in circuits up to 30 GHz and suitable for low noise and medium power amplifier application including a wide range of commercial and military application. All devices are 100% DC tested to assure consistent quality. All bond pads are gold plated for either thermo-compression or thermo-sonic wire bonding.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$)

Symbol	Conditions	MIN	TYP	MAX	UNIT
NF	Noise Figure at $V_{DS} = 2$ V, $I_{DS} = 10$ mA, $f = 12$ GHz		0.5	0.7	dB
G_a	Associated Gain at $V_{DS} = 2$ V, $I_{DS} = 10$ mA, $f = 12$ GHz	11	13		dB
P_{1dB}	Output Power at 1dB Gain Compression Point, $f = 12$ GHz, $V_{DS} = 6$ V, $I_{DS} = 25$ mA	17.5	18.5		dBm
G_L	Linear Power Gain, $f = 12$ GHz, $V_{DS} = 6$ V, $I_{DS} = 25$ mA	14	15		dB
I_{DSS}	Saturated Drain-Source Current at $V_{DS} = 2$ V, $V_{GS} = 0$ V		48		mA
g_m	Transconductance at $V_{DS} = 2$ V, $V_{GS} = 0$ V		55		mS
V_P	Pinch-off Voltage at $V_{DS} = 2$ V, $I_D = 0.32$ mA		-1.0*		Volts
BV_{DGO}	Drain-Gate Breakdown Voltage at $I_{DGO} = 0.08$ mA	9	12		Volts
R_{th}	Thermal Resistance		180		$^\circ\text{C}/\text{W}$

Note: * For the tight control of the pinch-off voltage. TC1101V's are divided into 3 groups:

(1) **TC1101VP0710** : $V_p = -0.7$ V to -1.0 V (2) **TC1101VP0811** : $V_p = -0.8$ V to -1.1 V

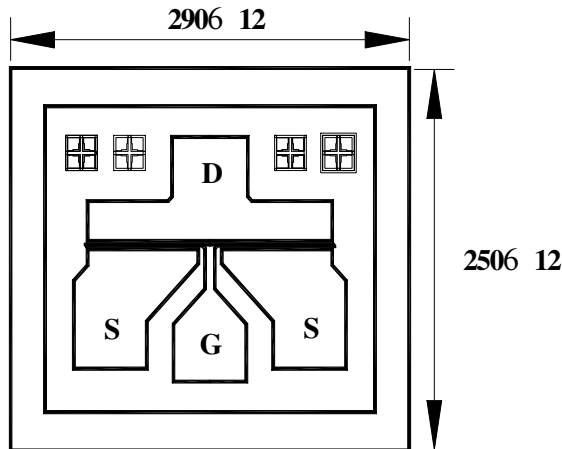
(3) **TC1101VP0912** : $V_p = -0.9$ V to -1.2 V

In addition, the customers may specify their requirements.

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$) TYPICAL NOISE PARAMETERS ($T_A = 25^\circ\text{C}$)

$V_{DS} = 2$ V, $I_{DS} = 10$ mA

Symbol	Parameter	Rating	Frequency (GHz)	NF_{opt} (dB)	G_A (dB)	Γ_{opt}		Rn/50
						MAG	ANG	
V_{DS}	Drain-Source Voltage	7.0 V	2	0.34	21.2	0.97	14	0.63
V_{GS}	Gate-Source Voltage	-3.0 V	4	0.36	19.3	0.83	30	0.54
I_{DS}	Drain Current	I_{DSS}	6	0.38	17.5	0.68	50	0.42
I_{GS}	Gate Current	160 μA	8	0.42	15.9	0.51	75	0.30
P_{in}	RF Input Power, CW	18 dBm	10	0.48	14.4	0.38	106	0.18
P_T	Continuous Dissipation	250 mW	12	0.54	13.2	0.28	145	0.14
T_{CH}	Channel Temperature	175 $^\circ\text{C}$	14	0.63	12.7	0.25	-168	0.12
T_{STG}	Storage Temperature	- 65 $^\circ\text{C}$ to +175 $^\circ\text{C}$	16	0.76	12.5	0.31	-111	0.17
			18	0.94	12.2	0.49	-45	0.36

CHIP DIMENSIONS**Units: Micrometers****Chip Thickness: 55****Gate Pad: 55 x 50****Drain Pad: 55 x 50****Source Pad: 55 x 60****CHIP HANDLING**

DIE ATTACHMENT : Conductive epoxy or eutectic die attach is recommended. For eutectic die attach can be accomplished with Au-Sn (80%Au-20%Sn) perform in State Temperature : 290°C \pm 5°C ; Handling Tool : Tweezers ; Time : less than 1min .

WIRE BONDING : The recommended wire bond method is thermocompression bonding with 0.7 or 1.0 mil (0.018 or 0.025mm) gold wire. State Temperature : 220°C to 250°C ; Bond Tip Temperature : 150°C ; Bond Force : 20 to 30 gms depending on size of wire and Bond Tip Temperature.

HANDLING PRECAUTIONS : The user must operate in a clean, dry environment. Care should be exercised during handling avoid damage to the devices. Electrostatic Discharge(ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. The static discharge must less than 300V.